

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N5817

1N5818

1N5819

SCHOTTKY BARRIER RECTIFIER

JEDEC D0-41 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N5817 Series types are Schottky Barrier Rectifiers mounted in an axial lead epoxy case using a metal to silicon junction to yield low forward voltage drop and instantaneous reverse recovery times.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	1N5817	1N5818	1N5819	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	20	30	40	V
DC Blocking Voltage	V_R	20	30	40	V
RMS Reverse Voltage	$V_R(RMS)$	14	21	28	V
Average Forward Surge Current ($T_L=100^\circ\text{C}$)	I_0		1.0		A
Peak Forward Surge Current	I_{FSM}		25		A
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +150			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	1N5817		1N5818		1N5819		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I_R	$V_R=V_{RRM}$		1.0		1.0		1.0	mA
I_R	$V_R=V_{RRM}, T_A=100^\circ\text{C}$		10		10		10	mA
V_F	$I_F=0.1\text{A}$		0.320		0.330		0.340	V
V_F	$I_F=1.0\text{A}$		0.450		0.550		0.600	V
V_F	$I_F=3.1\text{A}$		0.750		0.875		0.900	V